TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2 S A 1 9 4 2

POWER AMPLIFIER APPLICATIONS.

- Complementary to 2SC5199
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-180	V
Collector-Emitter Voltage	v_{CEO}	-180	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	$I_{\mathbf{C}}$	-12	A
Base Current	I_{B}	-1.2	A
Collector Power Dissipation (Tc=25°C)	$P_{\mathbf{C}}$	120	w
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$T_{ m stg}$	-55~150	°C

Unit in mm $\phi 3.3 \pm 0.2$ 20.5MAX 5.45 ± 0.15 +0.25 BASE COLLECTOR (HEAT SINK) 2. **EMITTER JEDEC EIAJ** TOSHIBA 2-21F1A

Weight: 9.75g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -180V, I_{E} = 0$		_	-5.0	μ A
Emitter Cut-off Current	${ m I}_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	<u> </u>	_	-5.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{C} = -50 \text{mA}, I_{B} = 0$	-180	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{CE} = -5V, I_{C} = -1A$	55	_	160	
	h _{FE (2)}	$V_{CE} = -5V, I_{C} = -6A$	35	80	_	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	$I_{C} = -8A, I_{B} = -0.8A$	_	-0.9	-2.5	V
Base-Emitter Voltage	$v_{ m BE}$	$V_{CE} = -5V, I_{C} = -6A$	_	-1.0	-1.5	V
Transition Frequency	${ m f_T}$	$V_{CE} = -5V$, $I_{C} = -1A$	_	30	_	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = -10V, I_{E} = 0, f = 1MHz$	_	360	_	pF

Note: hFE(1) Classification R:55~110, O:80~160

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